



General Description

The WSR4N65F is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR7N65F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

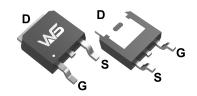
Product Summery

BV _{DSS}	R _{DSON}	I _D
650V	2.6Ω	4A

Applications

- AC/DC Power Conversion in Switched Mode Power Supplies (SMPS).
- Uninterruptible Power Supply(UPS)
- Adapter.

TO-252 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	4	Α
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ^{1.5}	2.5	А
I _{DM}	Pulsed Drain Current ^{1.2.5}	16	А
EAS	Single Pulse Avalanche Energy ¹	128	mJ
P _D	Total Power Dissipation ^{1,5}	77	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$ C
T _J	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		1.62	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	650			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =250uA		0.6		V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =3.5A		2.6	3.0	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} . In =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , IB -250UA		-4.57		mV/℃
	Danier Courses I and a second	V_{DS} =650V , V_{GS} =0V , T_J =25 $^{\circ}$ C			1	- uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =520V , V _{GS} =0V , T _J =55℃			10	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm30V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =40V , I _D =3.5A		5		S
Qg	Total Gate Charge (10V)	V _{DS} =520V , V _{GS} =10V , I _D =7A		10.2		
Q _{gs}	Gate-Source Charge			2.3		nC
Q _{gd}	Gate-Drain Charge			2.1		
T _{d(on)}	Turn-On Delay Time	V_{DD} =300V , V_{GS} =10V , R_{G} =25 Ω , I_{D} =10A.		15.5		
T _r	Rise Time			13		
T _{d(off)}	Turn-Off Delay Time			40		ns
T _f	Fall Time			16		
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , f=1MHz		550		
Coss	Output Capacitance			46		pF
C _{rss}	Reverse Transfer Capacitance			2.3		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,2,5}	V =V =0V Force Current			4	Α
I _{SM}	Pulsed Source Current ^{1,2}	V _G =V _D =0V , Force Current			16	Α
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V , I _S =7A , T _J =25℃			1.4	V
t _{rr}	Reverse Recovery Time			454		nS
Q _{rr}	Reverse Recovery Charge	lF=7A,dl/dt=40A/µs,Tյ=25℃		2076		nC

Notes:

Note 1 : limited by maximum junction temperature.

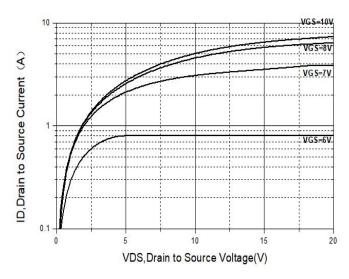
Note 2 : Bond wire current limit. Note 3 : V_{DS} =520V, I_{D} =4A.

Note 4 : I_D =0.5A, V_{DD} =50V, T_j =25°C.

Note 5: Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Characteristics

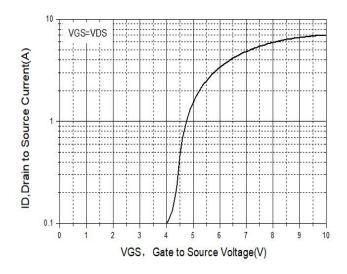


Rdson, Drain to Source on Resistance(Ω) ID, Drain Current(A)

VGS=10V

Figure 1 Output Characteristics

Figure 3 Rdson-ID Characteristics



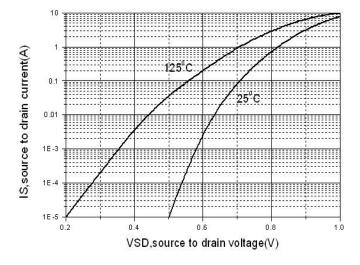


Figure 2 Transfer Characteristics

Figure 4 Body diode Characteristics



Typical Characteristics

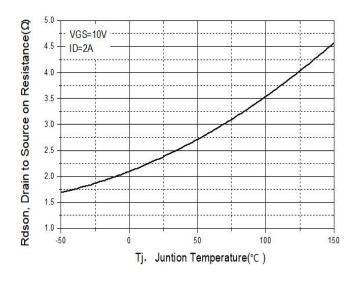


Figure 5 Rdson-Tj Relation

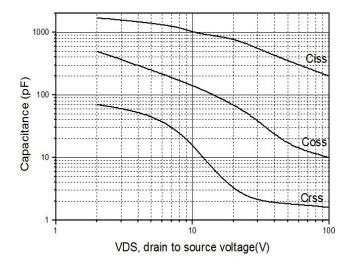


Figure 7 Capacitance vs Vds

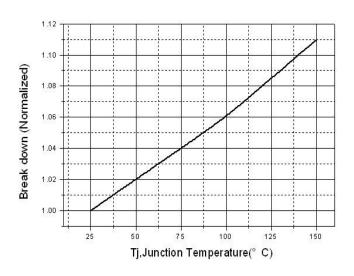


Figure 6 BVDSS vs Junction Temperature

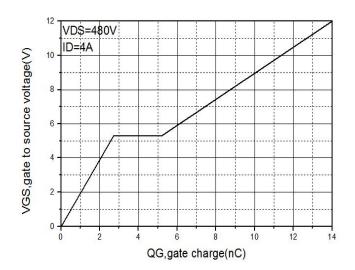
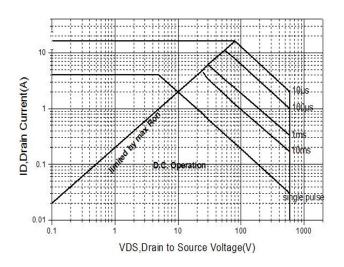


Figure 8 VGS vs QG Characteristics



Typical Characteristics



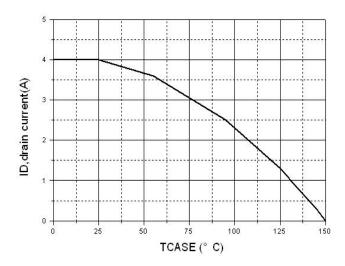


Figure 9 Safe Operation Area

Figure 10 Maximum current attenuation

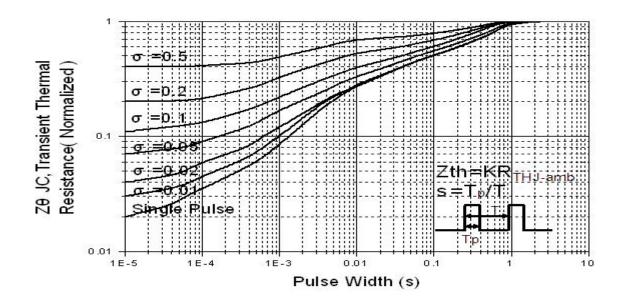


Figure 11 Normalized Maximum Transient Thermal Impedance



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